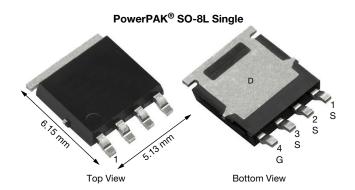


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Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



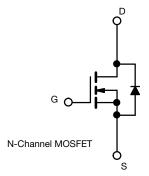
PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.0048
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0039
I _D (A)	60
Configuration	Single
Package	PowerPAK SO-8L

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ROHS COMPLIANT HALOGEN FREE



PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage	V _{DS}	40	V		
Gate-source voltage	V _{GS}	± 20			
Continuous drain current	T _C = 25 °C ^a	1	60		
	T _C = 125 °C	I _D	48		
Continuous source current (diode conduction	on)	I _S	44	Α	
Pulsed drain current ^b		I _{DM}	220		
Single pulse avalanche current	lse avalanche current		29		
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	42	mJ	
Maximum power dissipation ^b	T _C = 25 °C	D	68	W	
	T _C = 125 °C	P_{D}	22	VV	
Operating junction and storage temperature	T _J , T _{stg}	-55 to +175	°C		
Soldering recommendations (peak tempera	-	260	٠.		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	R_{thJA}	70	°C/W
Junction-to-case (drain)		R_{thJC}	3.1	C/VV

Notes

- a. Pakcage limited
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu A$		1.9	2.4	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}$	-	-	1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	300	
On-state drain current a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	20	-	-	Α
Drain-source on-state resistance ^a	, ,	V _{GS} = 4.5 V	I _D = 8 A	-	0.0040	0.0048	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A	-	0.0032	0.0039	Ω
		V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	-	-	0.0057	
		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	0.0067	
Forward transconductance b	9fs	V _{DS}	= 15 V, I _D = 10 A	-	51	-	S
Dynamic ^b							
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	2839	3900	pF
Output capacitance	Coss	$V_{GS} = 0 V$		-	888	1250	
Reverse transfer capacitance	C _{rss}	1		-	27	40	
Total gate charge ^c	Qg		V _{DS} = 20 V, I _D = 1 A	-	48.2	75	nC
Gate-source charge c	Q _{gs}	V _{GS} = 10 V		-	7.1	-	
Gate-drain charge ^c	Q_{gd}	1		-	8	-	
Gate resistance	R_g	f = 1 MHz		0.55	1.10	1.65	Ω
Turn-on delay time ^c	t _{d(on)}	$V_{DD} = 20 \text{ V}, \text{ R}_L = 20 \Omega$ $I_D \cong 1 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	14	25	- ns
Rise time ^c	t _r			-	5	10	
Turn-off delay time c	t _{d(off)}			-	35	55	
Fall time ^c	t _f			-	57	90	
Source-Drain Diode Ratings and Charac	teristics b						
Pulsed current a	I _{SM}			-	-	220	Α
Forward voltage	V _{SD}	I _F = 10 A, V _{GS} = 0		-	0.76	1.2	V
Body diode reverse recovery time	t _{rr}			-	39	80	ns
Body diode reverse recovery charge	Q _{rr}	I _F = 1 A, di/dt = 100 A/μs		-	46	95	nC
Reverse recovery fall time	ta			-	23	-	
Reverse recovery rise time	t _b			-	16	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			-	-2.1	-	Α

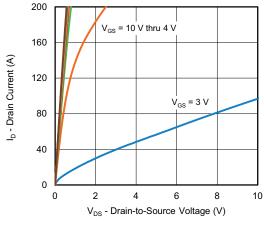
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

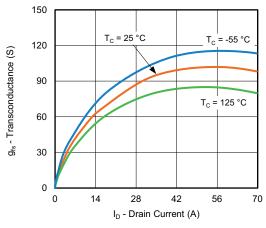
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



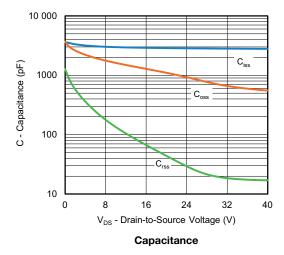
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

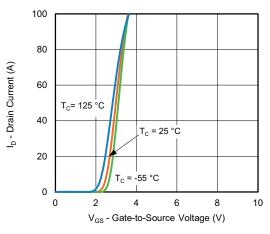


Output Characteristics

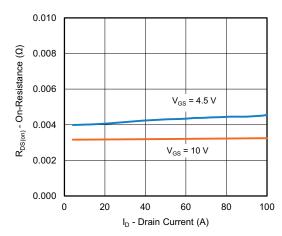


Transconductance

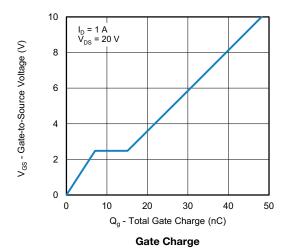




Transfer Characteristics

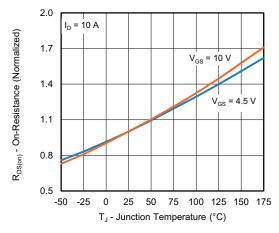


On-Resistance vs. Drain Current

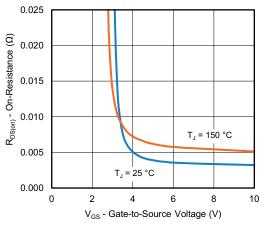




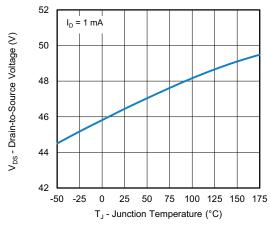
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



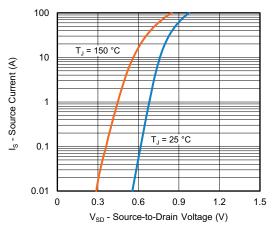
On-Resistance vs. Junction Temperature



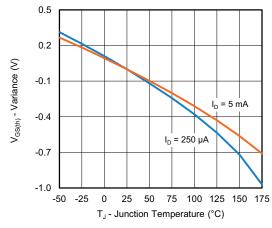
On-Resistance vs. Gate-to Source Voltage



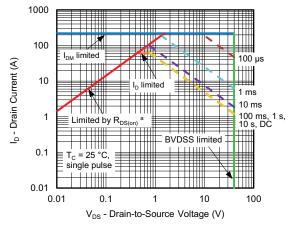
Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



Threshold Voltage



Safe Operating Area

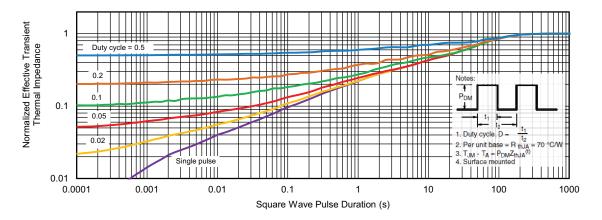
Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

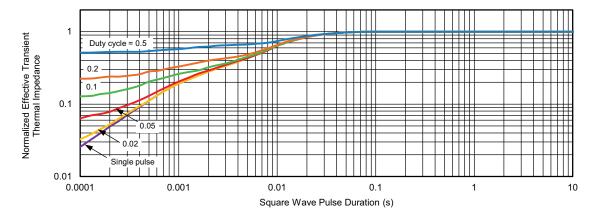
For technical questions, contact: automostech



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77332.



PowerPAK® SO-8L Case Outline 2



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DIM		MILLIMETERS		INCHES			
DIM.	MIN. NOM. MAX.			MIN. NOM. MAX			
Α	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
E3	6.05	6.22	6.40	0.238	0.245	0.252	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W	0.23			0.009			
W1		0.41			0.016		
W2	2.82			0.111			
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

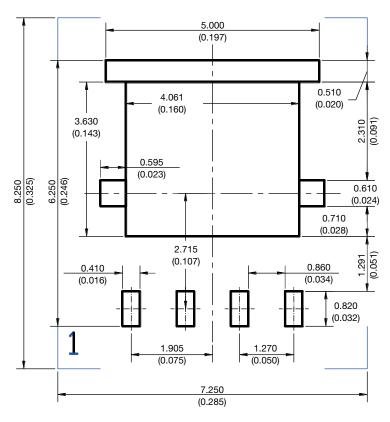
DWG: 6044

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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